

100V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI8080-5

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Tc = +25°C
100V	$1.5 \text{m}\Omega$ @ V _{GS} = 10V	352A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine management systems
- · Body control electronics
- DC-DC converters

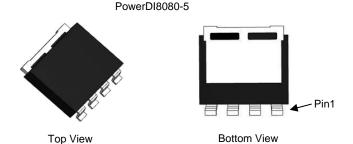
Features and Benefits

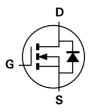
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production
 Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Rds(ON) Minimizes Power Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH10H1M7SPGWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

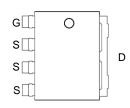
Mechanical Data

- Package: PowerDI[®]8080-5
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.36 grams (Approximate)





Internal Schematic



Top View
Pin Configuration

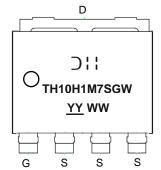
Ordering Information (Note 4)

Orderable Part Number	Package	Packing		
Orderable Fart Number	Fackage	Qty.	Carrier	
DMTH10H1M7SPGWQ-13	PowerDI8080-5	2,000	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ → H = Manufacturer's Marking

TH10H1M7SGW = Product Type Marking Code

YYWW = Date Code Marking

YY = Year (ex: 25 = 2025)

WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6)	Tc = +25°C Tc = +100°C	I _D	352 249	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	352	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	1400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	1400	Α
Avalanche Current, L = 1mH		las	53	Α
Avalanche Energy, L = 1mH		Eas	1404	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	5	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	30	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	405	W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	0.37	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Cumbal	Min	Turn	May	l lmi4	Toot Condition	
Characteristic OFF CHARACTERISTICS (Note 7)	Symbol	Min	Тур	Max	Unit	Test Condition	
	D\/	100	1		1/	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Drain-Source Breakdown Voltage	BV _{DSS}	100	_		V	$V_{GS} = 0$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 80V$, $V_{GS} = 0$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.13	1.5	mΩ	V _{GS} = 10V, I _D = 25A	
Diode Forward Voltage	VsD		0.75	1.2	V	V _G S = 0, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	10881			$V_{DS} = 50V, V_{GS} = 0,$ f = 1MHz	
Output Capacitance	Coss		3693	_	pF		
Reverse Transfer Capacitance	Crss	_	101	_			
Gate Resistance	Rg	_	0.71		Ω	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1MHz$	
Total Gate Charge	Qg		171			V _{DD} = 50V, I _D = 25A, V _{GS} = 10V	
Gate-Source Charge	Qgs		51	_	nC		
Gate-Drain Charge	Q_{gd}	_	40	_			
Turn-On Delay Time	tD(ON)	_	28	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 25A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	_	43		no		
Turn-Off Delay Time	t _{D(OFF)}	_	71	_	ns		
Turn-Off Fall Time	tF		54				
Body Diode Reverse-Recovery Time	trr	_	99	_	ns	1- 25A di/dt - 100A/ug	
Body Diode Reverse-Recovery Charge	Q _{RR}	_	334	_	nC	- I _F = 25A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

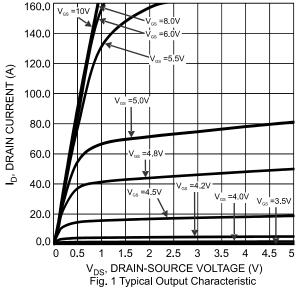
^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.







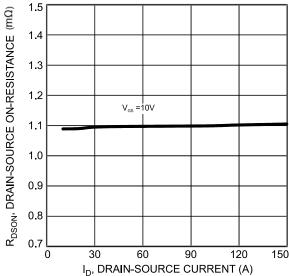


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

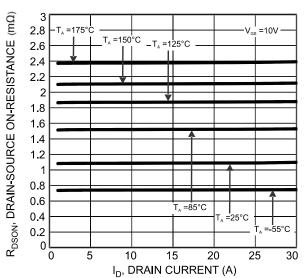
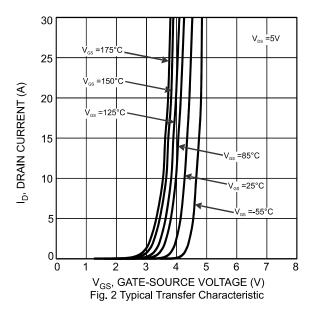
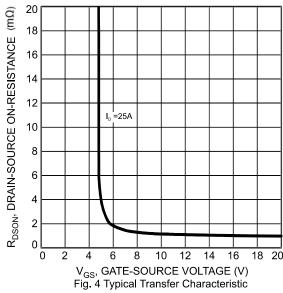


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature





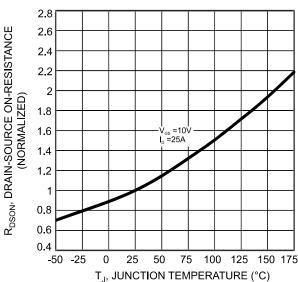
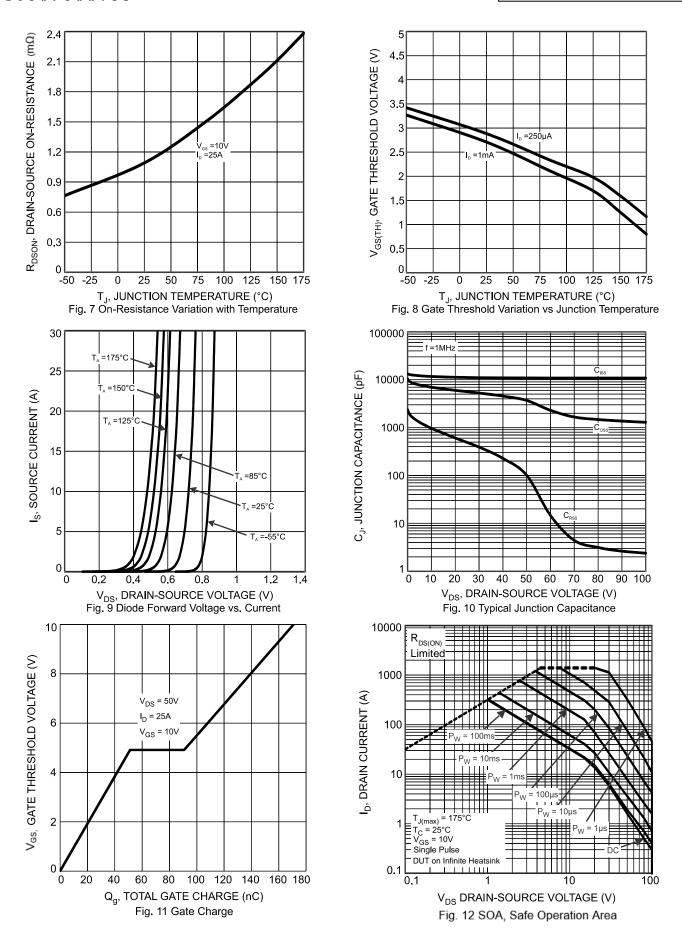


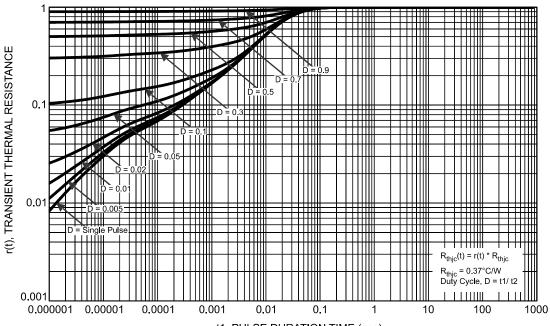
Fig. 6 On-Resistance Variation with Temperature











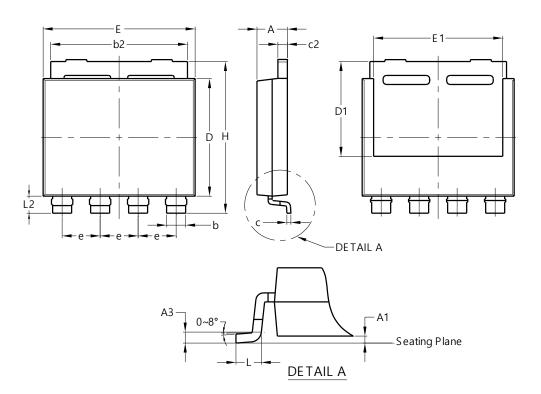
t1, PULSE DURATION TIME (sec) Fig. 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI8080-5

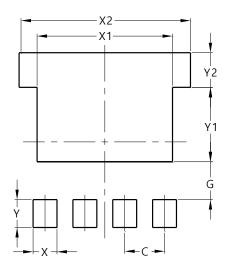


PowerDI8080-5				
Dim	Min	Max	Тур	
Α	1.50	1.70		
A1	0.00	0.15		
A3			0.25	
b	0.90	1.10		
b2	7.10	7.30		
С	0.18	0.24		
c2	0.47	0.57		
D	6.10	6.30		
D1	4.90	5.10		
Е	7.90	8.10		
E1	6.70	6.90		
е			2.00	
Н	7.80	8.10		
L	0.60	0.80		
L2	0.90	1.30		
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI8080-5



Dimensions	Value		
Dimonorono	(in mm)		
С	2.00		
G	1.90		
Χ	1.20		
X1	6.80		
X2	8.60		
Υ	1.40		
Y1	3.74		
Y2	1.76		



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